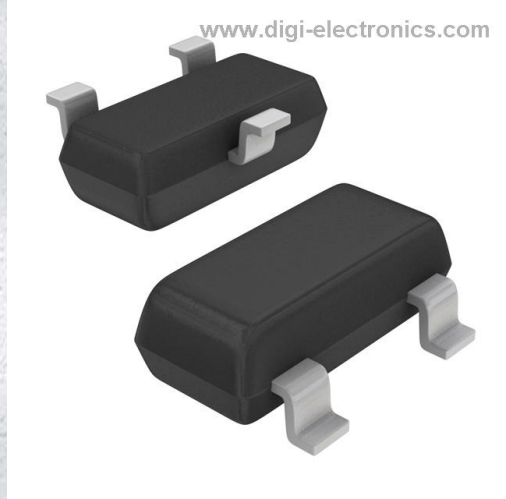
MMBTA63LT1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number	MMBTA63LT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	MMBTA63LT1G
Description	TRANS PNP DARL 30V 0.5A SOT23-3
Detailed Description	Bipolar (BJT) Transistor PNP - Darlington 30 V 500 mA 125MHz 225 mW Surface Mount SOT-23-3 (TO-236)

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MMBTA63LT1G	onsemi
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Darlington	500 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
30 V	1.5V @ 100µA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	5000 @ 100mA, 5V
Power - Max:	Frequency - Transition:
225 mW	125MHz
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3 (TO-236)
Base Product Number:	
MMBTA63	

Environmental & Export classification

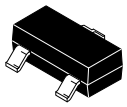
RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

DATA SHEET
www.onsemi.com

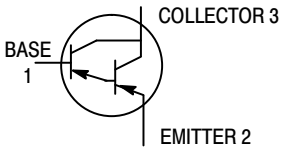
Darlington Transistors

PNP Silicon

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,



SOT−23 (TO−236)
CASE 318
STYLE 6



Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CES}	−30	Vdc
Collector − Base Voltage	V_{CBO}	−30	Vdc
Emitter − Base Voltage	V_{EBO}	−10	Vdc
Collector Current − Continuous	I_C	−500	mAdc

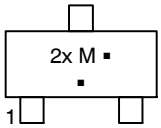
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

MARKING DIAGRAM



2x = Device Code
x = U for MMBTA63LT1G
x = V for MMBTA64LT1G
SMMBTA64LT1G
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA63LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBTA64LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBTA64LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I_C = −100 μAdc)	$V_{(BR)CEO}$	−30	–	Vdc
Collector Cutoff Current (V_{CB} = −30 Vdc)	I_{CBO}	–	−100	nAdc
Emitter Cutoff Current (V_{EB} = −10 Vdc)	I_{EBO}	–	−100	nAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3)	h_{FE}			–
(I_C = −10 mAdc, V_{CE} = −5.0 Vdc) MMBTA63		5,000	–	
(I_C = −10 mAdc, V_{CE} = −5.0 Vdc) MMBTA64, SMMBTA64		10,000	–	
(I_C = −100 mAdc, V_{CE} = −5.0 Vdc) MMBTA63		10,000	–	
(I_C = −100 mAdc, V_{CE} = −5.0 Vdc) MMBTA64, SMMBTA64		20,000	–	
Collector – Emitter Saturation Voltage (I_C = −100 mAdc, I_B = −0.1 mAdc)	$V_{CE(sat)}$	–	−1.5	Vdc
Base – Emitter On Voltage (I_C = −100 mAdc, V_{CE} = −5.0 Vdc)	$V_{BE(on)}$	–	−2.0	Vdc
SMALL– SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I_C = −10 mAdc, V_{CE} = −5.0 Vdc, f = 100 MHz)	f_T	125	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

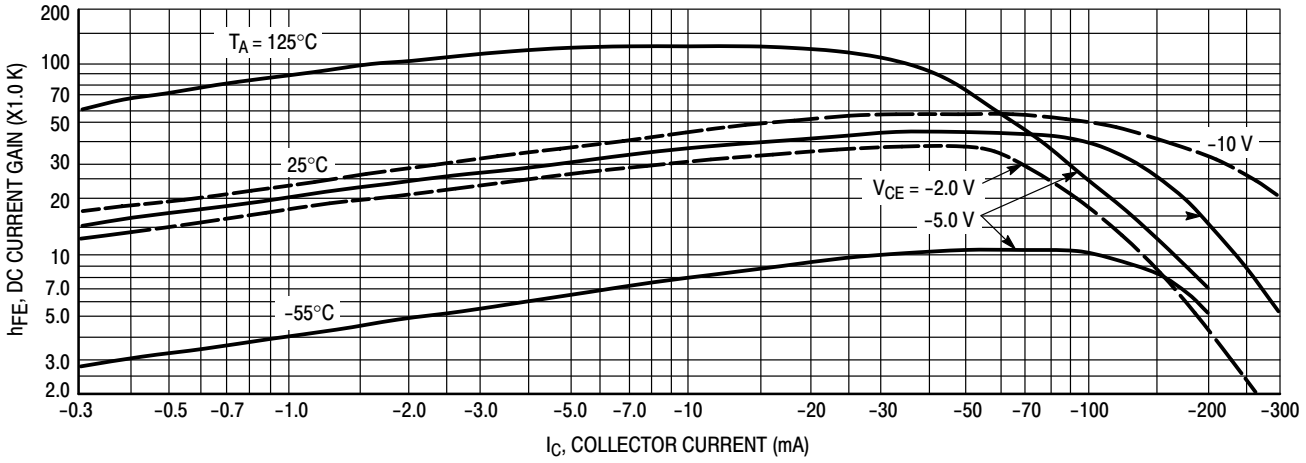


Figure 1. DC Current Gain

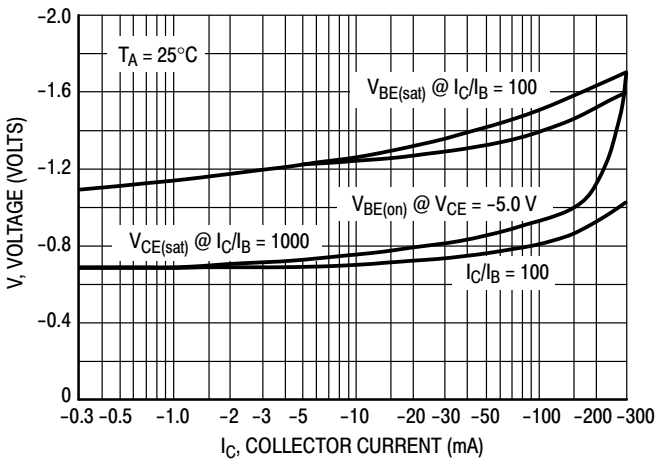


Figure 3. "On" Voltage

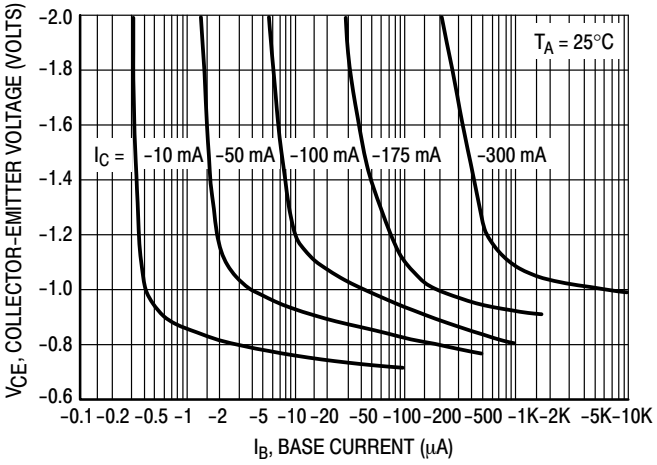


Figure 2. Collector Saturation Region

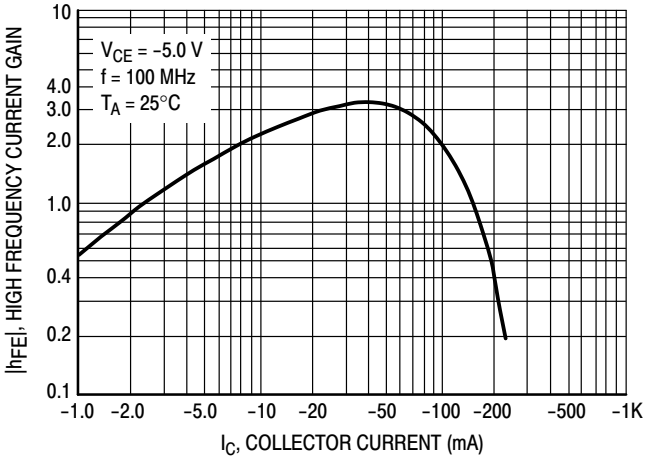


Figure 4. High Frequency Current Gain

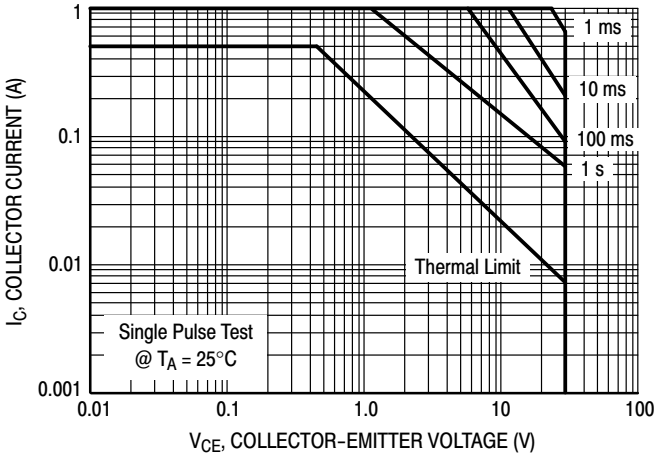
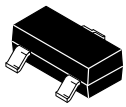


Figure 5. Safe Operating Area

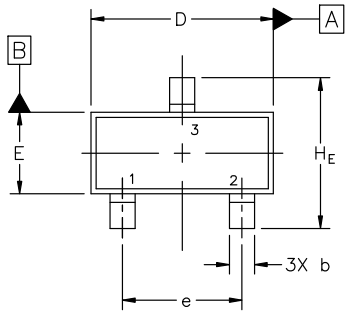
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



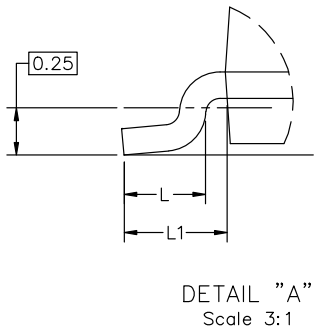
SCALE 4:1

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

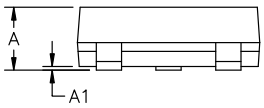
DATE 14 AUG 2024



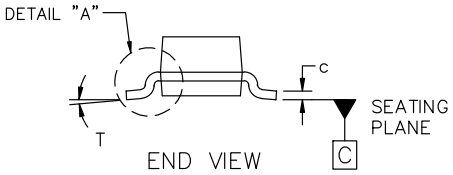
TOP VIEW



DETAIL "A"
Scale 3:1



SIDE VIEW

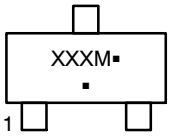


END VIEW

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
H_E	2.10	2.40	2.64
T	0°	−−−	10°

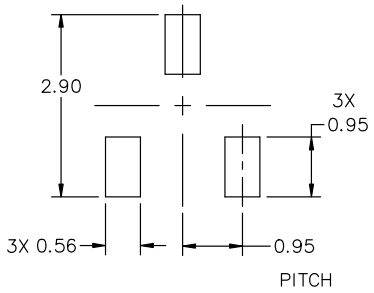
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOT−23 (TO−236) 2.90x1.30x1.00 1.90P**		**PAGE 1 OF 2**

SOT−23 (TO−236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

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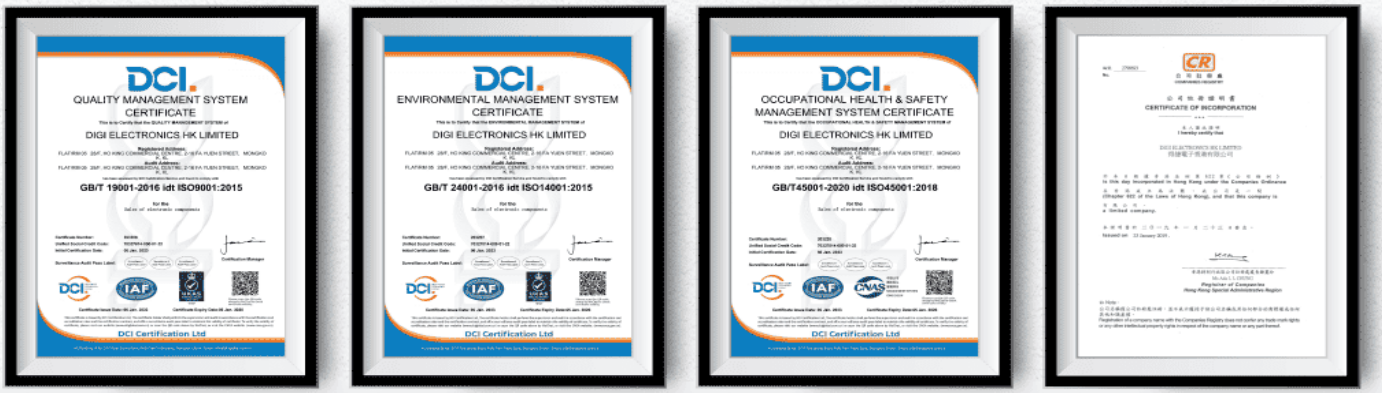

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